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CONFIRMATION NO. 2545

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## APPLICANTS

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## \*\* CONTINUING DATA \*\*\*\*\*

This application is a DIV of 08/685,789 07/24/1996 PAT 6,156,627  
which is a CON of 08/420,472 04/12/1995 ABN*ver.f: ed . SP*

## \*\* FOREIGN APPLICATIONS \*\*\*\*\*

JAPAN 6-100641 04/13/1994

*verified SP*

## IF REQUIRED, FOREIGN FILING LICENSE GRANTED

\*\* 01/02/2001

Foreign Priority claimed	<input checked="" type="checkbox"/> yes <input type="checkbox"/> no	STATE OR COUNTRY	SHEETS	TOTAL CLAIMS	INDEPENDENT CLAIMS
35 USC 119 (a-d) conditions met	<input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance	JAPAN	5	18	6
Verified and Acknowledged	<i>[Signature]</i> <i>[Initials]</i>				

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## TITLE

Method for forming semiconductor device

*EP 5-26-05*

*Method of Forming Device by Crystallizing Amorphous Silicon and Forming Crystallization Promoting Material in the Same Chamber*

<input type="checkbox"/> All Fees
<input type="checkbox"/> 1.16 Fees ( Filing )